Mikhail Baklanov

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/7026109/publications.pdf

Version: 2024-02-01

323	9,015	66343	54911
papers	citations	42 h-index	84 g-index

335	335	335	5378
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Methylated porous low-k materials: critical properties and plasma resistance. , 2022, , .		0
2	Charge Transport Mechanism in a PECVD Deposited Low-k SiOCH Dielectric. Journal of Electronic Materials, 2022, 51, 2521-2527.	2.2	1
3	Effect of H atoms and UV wideband radiation on cured low-k OSG films. Journal Physics D: Applied Physics, 2022, 55, 255206.	2.8	1
4	In-Situ Imaging of a Light-Induced Modification Process in Organo-Silica Films via Time-Domain Brillouin Scattering. Nanomaterials, 2022, 12, 1600.	4.1	3
5	Modification of Porous Ultralow-‹i›k‹/i› Film by Vacuum Ultraviolet Emission. ACS Applied Electronic Materials, 2022, 4, 2760-2776.	4.3	3
6	Charge Transport Mechanism and Trap Origin in Methylâ€Terminated Organosilicate Glass Lowâ€Î¹ Dielectrics. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000654.	1.8	2
7	Effect of methyl terminal and ethylene bridging groups on porous organosilicate glass films: FTIR, ellipsometric porosimetry, luminescence dataset. Data in Brief, 2021, 35, 106895.	1.0	3
8	Analytical Study of Porous Organosilicate Glass Films Prepared from Mixtures of 1,3,5- and 1,3-Alkoxysilylbenzenes. Materials, 2021, 14, 1881.	2.9	3
9	Mechanical Properties of Low-k Dielectric Deposited on Subtractively Patterned Cu Lines for Advanced Interconnects. , 2021, , .		0
10	Study on the Electrical, Structural, Chemical and Optical Properties of PVD Ta(N) Films Deposited with Different N2 Flow Rates. Coatings, 2021, 11, 937.	2.6	14
11	Atomic Structure and Optical Properties of Plasma Enhanced Chemical Vapor Deposited SiCOH Low-k Dielectric Film. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2021, 129, 645-651.	0.6	3
12	O2 plasma treated biosensor for enhancing detection sensitivity of sulfadiazine in a high-Đº HfO2 coated silicon nanowire array. Sensors and Actuators B: Chemical, 2020, 306, 127464.	7.8	15
13	Evaluation of Mechanical Properties of Porous OSG Films by PFQNM AFM and Benchmarking with Traditional Instrumentation. Langmuir, 2020, 36, 9377-9387.	3.5	23
14	Effects of Methyl Terminal and Carbon Bridging Groups Ratio on Critical Properties of Porous Organosilicate Glass Films. Materials, 2020, 13, 4484.	2.9	17
15	Critical properties and charge transport in ethylene bridged organosilica low-Î¹ dielectrics. Journal of Applied Physics, 2020, 127, .	2.5	12
16	Effect of terminal methyl group concentration on critical properties and plasma resistance of organosilicate low-k dielectrics. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	12
17	VUV radiation flux from argon DC magnetron plasma. Journal Physics D: Applied Physics, 2020, 53, 295202.	2.8	4
18	A detailed ellipsometric porosimetry and positron annihilation spectroscopy study of porous organosilicate-glass films with various ratios of methyl terminal and ethylene bridging groups. Microporous and Mesoporous Materials, 2020, 306, 110434.	4.4	11

#	Article	IF	Citations
19	Properties of organosilicate low-k films with 1,3- and 1,3,5-benzene bridges between Si atoms. Japanese Journal of Applied Physics, 2020, 59, SLLG01.	1.5	4
20	Superconductivity in a disordered metal with Coulomb interactions. Physical Review Research, 2020, 2, .	3.6	5
21	Charge transport mechanism in periodic mesoporous organosilica low-k dielectric. Applied Physics Letters, 2019, 115, 082904.	3.3	11
22	Effect of thickness scaling on the permeability and thermal stability of Ta(N) diffusion barrier. Applied Surface Science, 2019, 498, 143887.	6.1	12
23	Dependence of dielectric constant of hydrocarbon bridged low-k films on porosity. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 010601.	1.2	3
24	Effect of water content on the structural properties of porous methyl-modified silicate films. Journal of Sol-Gel Science and Technology, 2019, 92, 273-281.	2.4	15
25	Effect of the C-bridge on UV properties of organosilicate films. Thin Solid Films, 2019, 685, 329-334.	1.8	10
26	Elastic Scattering of Neutral Fluorine on Si, O, C, and H Atoms in the Range of the Relative Kinetic Energies of 2â€“200 eV. Technical Physics Letters, 2019, 45, 1187-1190.	0.7	0
27	Influence of Current Density on Orientation-Controllable Growth and Characteristics of Electrochemically Deposited Au Films. Journal of the Electrochemical Society, 2019, 166, D3232-D3237.	2.9	5
28	Impact of VUV photons on SiO2 and organosilicate low-k dielectrics: General behavior, practical applications, and atomic models. Applied Physics Reviews, 2019, 6, .	11.3	38
29	Characterization of PECVD ultralow dielectric constant porous SiOCH films using triethoxymethylsilane precursor and cinene porogen. Journal Physics D: Applied Physics, 2018, 51, 115103.	2.8	12
30	Synergistic effect of VUV photons and F atoms on damage and etching of porous organosilicate films. Plasma Processes and Polymers, 2018, 15, 1700213.	3.0	10
31	Silicon dioxide and low-kmaterial sputtering in dual frequency inductive discharge by argon ions with energies from 16 to 200 eV. Journal Physics D: Applied Physics, 2018, 51, 02LT02.	2.8	13
32	A non-destructive, fast evaluation of PVD diffusion barriers deposited on porous low-k dielectrics. Microelectronic Engineering, 2018, 198, 22-28.	2.4	5
33	Effect of terminal methyl groups concentration on properties of organosilicate glass low dielectric constant films. Japanese Journal of Applied Physics, 2018, 57, 07MC01.	1.5	20
34	Photoabsorption and damage of OSG lowâ€k films by VUV emission at 140â€“160â€‰nm. Plasma Processes and Polymers, 2018, 15, 1700166.	3.0	8
35	Plasma induced damage mitigation in spin-on self-assembly based ultra low-k dielectrics using template residues. Applied Physics Letters, 2017, 110, .	3.3	14
36	Cryogenic etching of porous low-k dielectrics in CF3Br and CF4 plasmas. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	1.2	19

#	Article	IF	Citations
37	Review of thin film porosity characterization approaches. , 2017, , .		1
38	Reentrant Resistive Behavior and Dimensional Crossover in Disordered Superconducting TiN Films. Scientific Reports, 2017, 7, 1718.	3.3	15
39	Experimental and DFT study of nitrogen atoms interactions with SiOCH low-Î² films. European Physical Journal D, 2017, 71, 1.	1.3	7
40	Damage and etching of ultra low-kmaterials in fluorocarbon plasma at lowered temperatures. Journal Physics D: Applied Physics, 2017, 50, 485202.	2.8	5
41	Study of CoTa alloy as barrier layer for Cu/low-kinterconnects. Journal Physics D: Applied Physics, 2017, 50, 405306.	2.8	16
42	Fluorine atoms interaction with the nanoporous materials: experiment and DFT simulation. European Physical Journal D, 2017, 71, 1.	1.3	12
43	Removal of organic template of mesoporous organosilicate thin films using supercritical carbon dioxide fluids. Japanese Journal of Applied Physics, 2017, 56, 07KF02.	1.5	2
44	Effect of Bridging and Terminal Alkyl Groups on Structural and Mechanical Properties of Porous Organosilicate Films. ECS Journal of Solid State Science and Technology, 2017, 6, N182-N188.	1.8	22
45	Low-k dielectrics for sub 10 nm technology node. , 2016, , .		1
46	Mitigation of plasma-induced damage in porous low-kdielectrics by cryogenic precursor condensation. Journal Physics D: Applied Physics, 2016, 49, 175203.	2.8	14
47	Effect of porosity and pore size on dielectric constant of organosilicate based low-k films: An analytical approach. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	18
48	Effect of the C-bridge length on the ultraviolet-resistance of oxycarbosilane low-k films. Applied Physics Letters, 2016, 108, .	3.3	11
49	Cu passivation for integration of gap-filling ultralow-k dielectrics. Applied Physics Letters, 2016, 109, 232901.	3.3	3
50	Influence of porosity on electrical properties of low-k dielectrics irradiated with vacuum-ultraviolet radiation. Applied Physics Letters, 2016, 109, 122902.	3.3	3
51	Surface-confined activation of ultra low-k dielectrics in CO2 plasma. Applied Physics Letters, 2016, 108, .	3.3	11
52	Low Dielectric Constant Materials for Nanoelectronics. Materials and Energy, 2016, , 163-271.	0.1	3
53	Multi-step reaction mechanism for F atom interactions with organosilicate glass and SiO_xfilms. Journal Physics D: Applied Physics, 2016, 49, 345203.	2.8	21
54	The effects of vacuum-ultraviolet radiation on defects in low-k organosilicate glass (SiCOH) as measured with electron-spin resonance. Thin Solid Films, 2016, 616, 23-26.	1.8	5

#	Article	IF	Citations
55	Comparison of vacuum ultra-violet emission of Ar/CF₄and Ar/CF₃I capacitively coupled plasmas. Plasma Sources Science and Technology, 2016, 25, 055001.	3.1	15
56	Dependence of electric potentials at trench surfaces on ion angular distribution in plasma etching processes. Journal Physics D: Applied Physics, 2016, 49, 105203.	2.8	2
57	Toward successful integration of gap-filling ultralow-k dielectrics. , 2016, , .		0
58	Laser anneal of oxycarbosilane low-k film. , 2016, , .		1
59	UV cure of oxycarbosilane low-k films. Microelectronic Engineering, 2016, 156, 103-107.	2.4	8
60	Supercritical carbon dioxide etching of transition metal (Cu, Ni, Co, Fe) thin films. Microelectronic Engineering, 2016, 153, 5-10.	2.4	9
61	Integration of porous low-kdielectrics using post porosity pore protection. Journal Physics D: Applied Physics, 2016, 49, 505105.	2.8	7
62	Damage free integration of ultralow-k dielectrics by template replacement approach. Applied Physics Letters, 2015, 107, .	3.3	20
63	Defect-induced bandgap narrowing in low-k dielectrics. Applied Physics Letters, 2015, 107, 082903.	3.3	27
64	Vacuum ultra-violet damage and damage mitigation for plasma processing of highly porous organosilicate glass dielectrics. Journal of Applied Physics, 2015, 118, .	2.5	22
65	Correlation between stress-induced leakage current and dielectric degradation in ultra-porous SiOCH low-k materials. Journal of Applied Physics, 2015, 118, .	2.5	12
66	Vacuum ultra-violet emission of CF₄and CF₃I containing plasmas and Their effect on low-k materials. Journal Physics D: Applied Physics, 2015, 48, 395202.	2.8	13
67	Influence of Milling Conditions on the Hydriding Properties of Mg-C Nanocomposites. Journal of Nanomaterials, 2015, 2015, 1-6.	2.7	4
68	Electrical Reliability Challenges of Advanced Low-k Dielectrics. ECS Journal of Solid State Science and Technology, 2015, 4, N3065-N3070.	1.8	44
69	Determination of the Model for the Chemical Structure of Porous PECVD Low-k Films. ECS Journal of Solid State Science and Technology, 2015, 4, N3140-N3145.	1.8	7
70	Optimized pore stuffing for enhanced compatibility with interconnect integration flow. , 2015, , .		1
71	Alternative integration of ultralow-k dielectrics by template replacement approach. , 2015, , .		0
72	Cryogenic etching processes applied to porous low-kmaterials using SF₆/C₄F₈plasmas. Journal Physics D: Applied Physics, 2015, 48, 435202.	2.8	18

#	Article	IF	Citations
73	Experimental and theoretical study of RF capacitively coupled plasma in Arâ€“CF₄â€“CF₃I mixtures. Plasma Sources Science and Technology, 2015, 24, 055006.	3.1	18
74	Study of porogen removal by atomic hydrogen generated by hot wire chemical vapor deposition for the fabrication of advanced low-k thin films. Thin Solid Films, 2015, 575, 103-106.	1.8	3
75	Advanced Interconnects: Materials, Processing, and Reliability. ECS Journal of Solid State Science and Technology, 2015, 4, Y1-Y4.	1.8	104
76	Modification of Ultra Low-k Dielectric Films by O₂and CO₂Plasmas. ECS Journal of Solid State Science and Technology, 2015, 4, N3048-N3057.	1.8	5
77	Improved Plasma Resistance for Porous Low-k Dielectrics by Pore Stuffing Approach. ECS Journal of Solid State Science and Technology, 2015, 4, N3098-N3107.	1.8	31
78	Stuffing-enabled surface confinement of silanes used as sealing agents on CF4 plasma-exposed 2.0 p-OSG films. Microelectronic Engineering, 2015, 137, 70-74.	2.4	7
79	Dependence of dielectric constant of SiOCH low-k films on porosity and pore size. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	13
80	Improvement of cohesion strength in ULK OSG materials by pore structure adjustment. Microelectronic Engineering, 2015, 137, 75-78.	2.4	4
81	Interaction of F atoms with SiOCH ultra-low-kfilms: I. Fluorination and damage. Journal Physics D: Applied Physics, 2015, 48, 175203.	2.8	23
82	Impact of carbon-doping on time dependent dielectric breakdown of SiO2-based films. Applied Physics Letters, 2015, 106, 072902.	3.3	15
83	Mechanical Stability of Porous Low-k Dielectrics. ECS Journal of Solid State Science and Technology, 2015, 4, N3058-N3064.	1.8	40
84	Interaction of F atoms with SiOCH ultra low-k films. Part II: etching. Journal Physics D: Applied Physics, 2015, 48, 175204.	2.8	17
85	Study of Wet Surface Activation Routes to Enable the Deposition of Monomolecular Organic Thin Films on k 2.0 Porous Dielectrics. ECS Journal of Solid State Science and Technology, 2014, 3, N3106-N3111.	1.8	7
86	Quantitative characterization of pore stuffing and unstuffing for postporosity plasma protection of low-k materials. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	17
87	The chemistry screening for ultra low-k dielectrics plasma etching. Proceedings of SPIE, 2014, , .	0.8	0
88	Low-k a-SiCO:H films as diffusion barriers for advanced interconnects. Microelectronic Engineering, 2014, 120, 221-224.	2.4	10
89	Pore sealing of k 2.0 dielectrics assisted by self-assembled monolayers deposited from vapor phase. Microelectronic Engineering, 2014, 120, 240-245.	2.4	24
90	Low-kfilms modification under EUV and VUV radiation. Journal Physics D: Applied Physics, 2014, 47, 025102.	2.8	47

#	Article	IF	Citations
91	Advanced PECVD SiCOH low-k films with low dielectric constant and/or high Youngâ€™s modulus. Microelectronic Engineering, 2014, 120, 225-229.	2.4	19
92	HF etching mechanisms of advanced low-k films. , 2014, , .		0
93	Impact of Plasma Pretreatment and Pore Size on the Sealing of Ultra-Low-k Dielectrics by Self-Assembled Monolayers. Langmuir, 2014, 30, 3832-3844.	3.5	28
94	Near-interfacial thermal donor generation during processing of (100)Si/low-Îº-Si-oxycarbide insulator structures revealed by electron spin resonance. Semiconductor Science and Technology, 2014, 29, 095008.	2.0	0
95	Mechanism of Modification of Fluorocarbon Polymer by Ultraviolet Irradiation in Oxygen Atmosphere. ECS Journal of Solid State Science and Technology, 2013, 2, N93-N98.	1.8	14
96	Metal-Organic Framework ZIF-8 Films As Low-Îº Dielectrics in Microelectronics. Chemistry of Materials, 2013, 25, 27-33.	6.7	227
97	Dual threshold diode based on the superconductor-to-insulator transition in ultrathin TiN films. Applied Physics Letters, 2013, 102, .	3.3	7
98	Development and evaluation of a-SiC:H films using a dimethylsilacyclopentane precursor as a low-k Cu capping layer. , 2013, , .		0
99	Sealed ultra low-k organosilica films with improved electrical, mechanical and chemical properties. Journal of Materials Chemistry C, 2013, 1, 3961.	5.5	8
100	Impact of wavelength of UV light and UV cure time on chemical and mechanical properties of PECVD deposited porous ultra low-k films. Microelectronic Engineering, 2013, 107, 134-137.	2.4	14
101	Electron spin resonance analysis of sputtering-induced defects in advanced low-Îº insulators (Îº=2.0â€“2.5). Microelectronic Engineering, 2013, 109, 240-243.	2.4	0
102	Magnetic field-induced dissipation-free state in superconducting nanostructures. Nature Communications, 2013, 4, 1437.	12.8	90
103	Modification of organosilicate glasses low-k films under extreme and vacuum ultraviolet radiation. Applied Physics Letters, 2013, 102, .	3.3	31
104	Plasma processing of low-k dielectrics. Journal of Applied Physics, 2013, 113, .	2.5	258
105	Chemisorption of ALD precursors in and on porous low-k films. Microelectronic Engineering, 2013, 106, 81-84.	2.4	15
106	High-resolution electron spin resonance analysis of ion bombardment induced defects in advanced low-Îº insulators (Îºâ€‰=â€‰2.0-2.5). Applied Physics Letters, 2013, 102, .	3.3	15
107	Atomic Layer Deposition of TiO₂ on Surface Modified Nanoporous Low-k Films. Langmuir, 2013, 29, 12284-12289.	3.5	19
108	Influence of porosity on dielectric breakdown of ultralow-k dielectrics. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 050604.	1.2	19

#	Article	IF	Citations
109	Effect of Pore Structure of Nanometer Scale Porous Films on the Measured Elastic Modulus. Langmuir, 2013, 29, 12025-12035.	3.5	47
110	Sealing of low-k dielectric (k=2.0) with self-assembled monolayers (SAMs) for the atomic layer deposition (ALD) of TiN. Materials Research Society Symposia Proceedings, 2013, 1559, 1.	0.1	2
111	Pore Narrowing of Mesoporous Silica Materials. Materials, 2013, 6, 570-579.	2.9	3
112	Low Damage Cryogenic Etching of Porous Organosilicate Low-k Materials Using SF₆/O₂/SiF₄. ECS Journal of Solid State Science and Technology, 2013, 2, N131-N139.	1.8	29
113	The Diffusion Mechanism of Polymer Transfer Through Nanopores. , 2013, , .		0
114	Characterization of Porous Structures in Advanced Low-kFilms with Thin TaN Layers Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2013, 52, 106501.	1.5	9
115	Trap spectroscopy and Ta penetration induced charge trapping in porous SiOCH low-k dielectrics. , 2013, , .		1
116	The Effects of Plasma Treatments and Subsequent Atomic Layer Deposition on the Pore Structure of a k = 2.0 Low-k Material. ECS Journal of Solid State Science and Technology, 2013, 2, N103-N109.	1.8	7
117	Damage Free Cryogenic Etching of a Porous Organosilica Ultralow-k Film. ECS Solid State Letters, 2012, 2, N5-N7.	1.4	31
118	Study of Chemical Vapor Deposition of Manganese on Porous SiCOH Low-k Dielectrics Using Bis(ethylcyclopentadienyl)manganese. Electrochemical and Solid-State Letters, 2012, 15, H176.	2.2	16
119	Intrinsic effect of porosity on mechanical and fracture properties of nanoporous ultralow-k dielectrics. Applied Physics Letters, 2012, 101, 123109.	3.3	32
120	Impact of curing condition on chemical stability of ultralow-k PMO material.. Materials Research Society Symposia Proceedings, 2012, 1428, 7.	0.1	2
121	Pore sealing of SiOCH ultra low-k dielectrics with polyimide Langmuir-Blodgett film. Materials Research Society Symposia Proceedings, 2012, 1428, 32.	0.1	1
122	Time dependent dielectric breakdown study of organo silicate glass materials over a wide range of k-values. , 2012, , .		3
123	Pore Sealing of Porous Ultralow-k Dielectrics by Self-Assembled Monolayers Combined with Atomic Layer Deposition. ECS Solid State Letters, 2012, 1, P42-P44.	1.4	23
124	In Situ Monitoring of Atomic Layer Deposition in Nanoporous Thin Films Using Ellipsometric Porosimetry. Langmuir, 2012, 28, 3852-3859.	3.5	51
125	Nanoscale Noncontact Subsurface Investigations of Mechanical and Optical Properties of Nanoporous Low-k Material Thin Film. ACS Nano, 2012, 6, 1410-1415.	14.6	59
126	A new procedure to seal the pores of mesoporous low-k films with precondensed organosilica oligomers. Chemical Communications, 2012, 48, 2797.	4.1	22

#	Article	IF	Citations
127	Superconducting phase transitions in ultrathin TiN films. Europhysics Letters, 2012, 97, 17012.	2.0	56
128	Nanoporous Dielectric Materials for Advanced Micro- and Nanoelectronics. NATO Science for Peace and Security Series B: Physics and Biophysics, 2012, , 3-18.	0.3	2
129	Interconnect materials challenges for sub 20 nm technology nodes: Ultra low-k dielectrics. , 2012, , .		0
130	Ultra-low-k cyclic carbon-bridged PMO films with a high chemical resistance. Journal of Materials Chemistry, 2012, 22, 8281.	6.7	44
131	Tuning the Pore Size of Ink-Bottle Mesopores by Atomic Layer Deposition. Chemistry of Materials, 2012, 24, 1992-1994.	6.7	59
132	Influence of porosity on electrical properties of low-k dielectrics. Microelectronic Engineering, 2012, 92, 59-61.	2.4	33
133	Spacious and mechanically flexible mesoporous silica thin film composed of an open network of interlinked nanoslabs. Journal of Materials Chemistry, 2011, 21, 7692.	6.7	24
134	Fundamental study of atomic layer deposition in and on porous low-k films. , 2011, , .		3
135	Effect of bake/cure temperature of an advanced organic ultra low-k material on the interface adhesion strength to metal barriers. Journal of Applied Physics, 2011, 109, .	2.5	16
136	Influence of Varying Porogen Loads and Different UV Cures on Low- Film Characteristics. Journal of Nanoscience and Nanotechnology, 2011, 11, 8363-8367.	0.9	0
137	Influence of the ion bombardment of O2 plasmas on low-k materials. Thin Solid Films, 2011, 520, 464-468.	1.8	9
138	Study of metal barrier deposition-induced damage to porous low-k materials. Microelectronic Engineering, 2011, 88, 3030-3034.	2.4	23
139	The influence of N containing plasmas on low-k films. Microelectronic Engineering, 2011, 88, 627-630.	2.4	6
140	Active species in porous media: Random walk and capture in traps. Microelectronic Engineering, 2011, 88, 694-696.	2.4	16
141	Integrated diffusionâ€“recombination model for describing the logarithmic time dependence of plasma damage in porous low-k materials. Microelectronic Engineering, 2011, 88, 631-634.	2.4	14
142	Effect of porogen residue on electrical characteristics of ultra low-k materials. Microelectronic Engineering, 2011, 88, 990-993.	2.4	42
143	Electron spin resonance study of defects in low-Î° oxide insulators (Î°=2.5â€“2.0). Microelectronic Engineering, 2011, 88, 1503-1506.	2.4	19
144	Effect of ultraviolet curing wavelength on low-k dielectric material properties and plasma damage resistance. Thin Solid Films, 2011, 519, 3619-3626.	1.8	26

#	Article	IF	Citations
145	Evaluation of a New Advanced Low-kMaterial. Japanese Journal of Applied Physics, 2011, 50, 05EB03.	1.5	12
146	Advanced Organic Polymer for the Aggressive Scaling of Low-k Materials. Japanese Journal of Applied Physics, 2011, 50, 04DB01.	1.5	11
147	Effect of UV wavelength on the hardening process of porogen-containing and porogen-free ultralow-k plasma-enhanced chemical vapor deposition dielectrics. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	1.2	37
148	Role of copper in time dependent dielectric breakdown of porous organo-silicate glass low-k materials. Applied Physics Letters, 2011, 99, 222110.	3.3	31
149	Direct observation of the 1/E dependence of time dependent dielectric breakdown in the presence of copper. Applied Physics Letters, 2011, 98, 032107.	3.3	43
150	The effect of He plasma treatment on properties of organosilicate glass low-k films. Journal of Applied Physics, 2011, 109, 043303-043303-11.	2.5	18
151	Defects in Low-k Insulators (Î²=2.5 â€“ 2.0): ESR Analysis and Charge Injection. Materials Research Society Symposia Proceedings, 2011, 1335, 119.	0.1	3
152	Ultra Low Dielectric Constant Materials for 22 nm Technology Node and Beyond. ECS Transactions, 2011, 35, 717-728.	0.5	1
153	Ultra Low-k Materials Based on Self-Assembled Organic Polymers. Materials Research Society Symposia Proceedings, 2011, 1335, 27.	0.1	0
154	Influence of the UV Cure on Advanced Plasma Enhanced Chemical Vapour Deposition Low-kMaterials. Japanese Journal of Applied Physics, 2011, 50, 05EB05.	1.5	5
155	Advanced Organic Polymer for the Aggressive Scaling of Low-kMaterials. Japanese Journal of Applied Physics, 2011, 50, 04DB01.	1.5	7
156	Evaluation of a New Advanced Low-kMaterial. Japanese Journal of Applied Physics, 2011, 50, 05EB03.	1.5	6
157	Influence of the UV Cure on Advanced Plasma Enhanced Chemical Vapour Deposition Low-kMaterials. Japanese Journal of Applied Physics, 2011, 50, 05EB05.	1.5	3
158	Disorder and vortex matching effects in nanoperforated ultrathin TiN films. Physica C: Superconductivity and Its Applications, 2010, 470, S808-S809.	1.2	2
159	Comment on â€œMELâ€type Pureâ€Silica Zeolite Nanocrystals Prepared by an Evaporationâ€Assisted Twoâ€Stage Synthesis Method as Ultraâ€Lowâ€k Materialsâ€• Advanced Functional Materials, 2010, 20, 2377-2379.	14.9	9
160	Effect of top power on a low-k film during oxygen strip in a TCP etch chamber. Microelectronic Engineering, 2010, 87, 462-465.	2.4	1
161	Capacitance measurements and k-value extractions of low-k films. Microelectronic Engineering, 2010, 87, 2391-2406.	2.4	54
162	Porogen residues detection in optical properties of low-k dielectrics cured by ultraviolet radiation. Thin Solid Films, 2010, 518, 4266-4272.	1.8	50

#	Article	IF	Citations
163	Influence of the Top Chamber Window Temperature on the STI Etch Process. ECS Transactions, 2010, 27, 731-736.	0.5	1
164	Effects of He Plasma Pretreatment on Low-k Damage during Cu Surface Cleaning with NH[sub 3] Plasma. Journal of the Electrochemical Society, 2010, 157, H565.	2.9	27
165	TaN metal gate etch mechanisms in BCl3-based plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 302-305.	2.1	8
166	Effect of energetic ions on plasma damage of porous SiCOH low-k materials. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 450-459.	1.2	30
167	Ultra Low-k Materials: Challenges of Scaling. ECS Transactions, 2010, 33, 117-123.	0.5	5
168	Pseudogap in a thin film of a conventional superconductor. Nature Communications, 2010, 1, 140.	12.8	149
169	Unusual Modification of CuCl or CuBr Films by He Plasma Exposure Resulting in Nanowire Formation. Langmuir, 2010, 26, 2014-2020.	3.5	3
170	The mechanism of low-k SiOCH film modification by oxygen atoms. Journal of Applied Physics, 2010, 108, .	2.5	53
171	Improving mechanical robustness of ultralow-k SiOCH plasma enhanced chemical vapor deposition glasses by controlled porogen decomposition prior to UV-hardening. Journal of Applied Physics, 2010, 107, .	2.5	81
172	Evaluation of plasma damage in blanket and patterned low-k structures by near-field scanning probe microwave microscope: effect of plasma ash chemistry. , 2009, , .		2
173	Effect of Porogen Residue on Chemical, Optical, and Mechanical Properties of CVD SiCOH Low-k Materials. Electrochemical and Solid-State Letters, 2009, 12, H292.	2.2	56
174	SELECTIVE REMOVAL OF HIGH-KGATE DIELECTRICS. Chemical Engineering Communications, 2009, 196, 1475-1535.	2.6	36
175	Optimization of low-k UV Curing: Effect of Wavelength on Critical Properties of the Dielectrics. Materials Research Society Symposia Proceedings, 2009, 1156, 1.	0.1	4
176	Effects of Silica Sources on Nanoporous Organosilicate Films Templated with Tetraalkylammonium Cations. Materials Research Society Symposia Proceedings, 2009, 1156, 1.	0.1	0
177	Interaction of O and H Atoms with low-k SiOCH films pretreated in He plasma. Materials Research Society Symposia Proceedings, 2009, 1156, 1.	0.1	2
178	Plasma etching: From micro- to nanoelectronics. High Energy Chemistry, 2009, 43, 204-212.	0.9	7
179	Characterization of spin-on zeolite films prepared from Silicalite-1 nanoparticle suspensions. Microporous and Mesoporous Materials, 2009, 118, 458-466.	4.4	20
180	Depth-profiling of elastic inhomogeneities in transparent nanoporous low-k materials by picosecond ultrasonic interferometry. Applied Physics Letters, 2009, 95, .	3.3	59

#	Article	IF	Citations
181	Recombination of O and H Atoms on the Surface of Nanoporous Dielectrics. IEEE Transactions on Plasma Science, 2009, 37, 1697-1704.	1.3	23
182	Optical properties of TiN thin films close to the superconductorâ€“insulator transition. New Journal of Physics, 2009, 11, 113017.	2.9	16
183	Characterization of Plasma Damage in Low-k Films by TVS Measurements. Materials Research Society Symposia Proceedings, 2009, 1156, 1.	0.1	3
184	Impact of plasma exposure on organic low-k materials. , 2009, , .		4
185	New properties of halogen plasma-treated Cu films. International Journal of Materials Research, 2009, 100, 826-829.	0.3	1
186	Effects of Bias, Pressure and Temperature in Plasma Damage of Ultra Low-k Films. Solid State Phenomena, 2008, 134, 317-320.	0.3	8
187	Spectroscopic ellipsometry and ellipsometric porosimetry studies of CVD lowâ€k dielectric films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1253-1256.	0.8	11
188	Stiffening and hydrophilisation of SOG lowâ€k material studied by ellipsometric porosimetry, UV ellipsometry and laserâ€induced surface acoustic waves. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 829-832.	1.8	17
189	Nanoporous Organosilicate Films Prepared in Acidic Conditions Using Tetraalkylammonium Bromide Porogens. Advanced Functional Materials, 2008, 18, 3332-3339.	14.9	9
190	Evidence of Large Voids in Pureâ€Silicaâ€Zeolite Lowâ€k Dielectrics Synthesized by Spinâ€on of Nanoparticle Suspensions. Advanced Materials, 2008, 20, 3110-3116.	21.0	34
191	Quantum-critical region of the disorder-driven superconductorâ€“insulator transition. Physica C: Superconductivity and Its Applications, 2008, 468, 316-321.	1.2	27
192	Oxygen chemiluminescence in He plasma as a method for plasma damage evaluation. Microelectronic Engineering, 2008, 85, 2164-2168.	2.4	1
193	Effect of pressure on efficiency of UV curing of CVD-derived low-k material at different wavelengths. Microelectronic Engineering, 2008, 85, 2094-2097.	2.4	72
194	Superinsulator and quantum synchronization. Nature, 2008, 452, 613-615.	27.8	193
195	Hyperactivated resistance in TiN films on the insulating side of the disorder-driven superconductor-insulator transition. JETP Letters, 2008, 88, 752-757.	1.4	23
196	Disorder-Induced Inhomogeneities of the Superconducting State Close to the Superconductor-Insulator Transition. Physical Review Letters, 2008, 101, 157006.	7.8	274
197	Zeolite-Inspired Low-kDielectrics Overcoming Limitations of Zeolite Films. Journal of the American Chemical Society, 2008, 130, 17528-17536.	13.7	36
198	Reaction of Trimethylchlorosilane in Spin-On Silicalite-1 Zeolite Film. Langmuir, 2008, 24, 4894-4900.	3.5	21

#	Article	IF	Citations
199	Ultraviolet-Assisted Curing of Organosilicate Glass Low-k Dielectric by Excimer Lamps. Journal of the Electrochemical Society, 2008, 155, G231.	2.9	22
200	Changes of UV Optical Properties of Plasma Damaged Low-k Dielectrics for Sidewall Damage Scatterometry. Materials Research Society Symposia Proceedings, 2008, 1079, 1.	0.1	4
201	Using Ellipsometry for Assessment of TiN Surface Roughness after Plasma Etch. Journal of the Electrochemical Society, 2008, 155, H108.	2.9	2
202	Plasma Modification Of Si-O-Si Bond Structure in Porous Sioch Films. Materials Research Society Symposia Proceedings, 2008, 1079, 1.	0.1	5
203	Optical Property Changes in Low-k Films upon Ultraviolet-Assisted Curing. Journal of the Electrochemical Society, 2008, 155, G115.	2.9	42
204	Optical characteristics and UV modification of low-k materials. , 2008, , .		2
205	Influence of absorbed water components on SiOCH low-k reliability. Journal of Applied Physics, 2008, 104, .	2.5	77
206	<title>Effect of quartz window temperature on plasma composition during STI etch</title>. Proceedings of SPIE, 2008, , .	0.8	0
207	Profile control of novel non-Si gates using BCl[sub 3]âˆ•N[sub 2] plasma. Journal of Vacuum Science & Technology B, 2007, 25, 739.	1.3	10
208	Damage Reduction and Sealing of Low-k Films by Combined He and NH[sub 3] Plasma Treatment. Electrochemical and Solid-State Letters, 2007, 10, G76.	2.2	38
209	Plasma ash modulation of TDDB thermal activation energy in damascene SiOC:H. Semiconductor Science and Technology, 2007, 22, 320-325.	2.0	3
210	Quantum Metallicity on the High-Field Side of the Superconductor-Insulator Transition. Physical Review Letters, 2007, 98, 127003.	7.8	76
211	Study of a Metal Gate and Silicon Selective â€œDry Ash Onlyâ€•Process for Combined Extension and Halo Implanted Photo Resist. Solid State Phenomena, 2007, 134, 113-116.	0.3	5
212	Ultra-violet-assisted cure of spin-on silicalite-1 films. Studies in Surface Science and Catalysis, 2007, 170, 594-599.	1.5	3
213	Localized Superconductivity in the Quantum-Critical Region of the Disorder-Driven Superconductor-Insulator Transition in TiN Thin Films. Physical Review Letters, 2007, 99, 257003.	7.8	174
214	Characterization of a Molecular Sieve Coating Using Ellipsometric Porosimetry. Langmuir, 2007, 23, 12811-12816.	3.5	43
215	Ultraviolet-Assisted Curing of Polycrystalline Pure-Silica Zeolites:â€‰ Hydrophobization, Functionalization, and Cross-Linking of Grains. Journal of the American Chemical Society, 2007, 129, 9288-9289.	13.7	38
216	Diffusion of solvents in thin porous films. Colloids and Surfaces A: Physicochemical and Engineering Aspects, 2007, 300, 111-116.	4.7	26

#	Article	IF	Citations
217	An investigation of ultra low-k dielectrics with high thermal stability for integration in memory devices. Microelectronic Engineering, 2007, 84, 2582-2586.	2.4	3
218	Surface properties restoration and passivation of high porosity ultra low-k dielectric (kâ‰¼2.3) after direct-CMP. Microelectronic Engineering, 2007, 84, 2620-2623.	2.4	8
219	Porous low dielectric constant materials for microelectronics. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2006, 364, 201-215.	3.4	112
220	Moisture Induced Degradation of Porous Low-k Materials. Materials Research Society Symposia Proceedings, 2006, 914, 1.	0.1	8
221	Effect of Surfactant as Additive in Wet Clean Solutions on Properties of Low-k Materials. Electrochemical and Solid-State Letters, 2006, 9, F17.	2.2	5
222	Quantification of processing damage in porous low dielectric constant films. Microelectronic Engineering, 2006, 83, 2287-2291.	2.4	56
223	Effect of the pore structure on the properties of nanoporous silsesquioxane thin film. Microporous and Mesoporous Materials, 2006, 94, 113-121.	4.4	12
224	Negative magnetoresistance and quantum oscillations in ultrathin perforated PtSi films. Physica B: Condensed Matter, 2006, 378-380, 1058-1059.	2.7	3
225	The etchback approach: Enlarged process window for MuGFET gate etching. Microelectronic Engineering, 2006, 83, 570-576.	2.4	2
226	Zeolite Low-k Film Properties Dependence on Nanocrystal Size. Materials Research Society Symposia Proceedings, 2006, 914, 1.	0.1	2
227	Low dielectric constant materials: challenges of plasma damage. , 2006, , .		10
228	Challenges in the implementation of low-k dielectrics in the back-end of line. Microelectronic Engineering, 2005, 80, 337-344.	2.4	99
229	Effect of silylation on triethoxyfluorosilane xerogel films by means of atmospheric pressure drying. Thin Solid Films, 2005, 471, 145-153.	1.8	17
230	Anomalous behavior near T c and synchronization of Andreev reflection in two-dimensional arrays of SNS junctions. JETP Letters, 2005, 81, 10-14.	1.4	13
231	From quantum corrections to magnetic-field-tuned superconductorâ€“insulator quantum phase transition in TiN films. Physica B: Condensed Matter, 2005, 359-361, 500-502.	2.7	32
232	Highly Sensitive Monitoring of Ru Etching Using Optical Emission. Electrochemical and Solid-State Letters, 2005, 8, G176.	2.2	3
233	Removal of Plasma-Modified Low-k Layer Using Dilute HF: Influence of Concentration. Electrochemical and Solid-State Letters, 2005, 8, F21.	2.2	37
234	Aggressive scaling of Cu/low k: impact on metrology. AIP Conference Proceedings, 2005, , .	0.4	1

#	Article	IF	Citations
235	HF Based Solutions for HfO₂ Removal; Effect of pH and Temperature on HfO₂: SiO₂ Etch Selectivity. Solid State Phenomena, 2005, 103-104, 97-102.	0.3	1
236	Effect of plasma treatments on a low-k dielectric polymer surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1551.	1.6	13
237	Minimizing plasma damage and in situ sealing of ultralow-k dielectric films by using oxygen free fluorocarbon plasmas. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2198.	1.6	19
238	Effect of Chemical Solution on the Stability of Low-k Films. Solid State Phenomena, 2005, 103-104, 349-352.	0.3	3
239	A theoretical and experimental study of atomic-layer-deposited films onto porous dielectric substrates. Journal of Applied Physics, 2005, 98, 083515.	2.5	16
240	Materials Characterization by Ellipsometry. , 2005, , 461-473.		2
241	Revealing the Porous Structure of Low-k Materials Through Solvent Diffusion. , 2005, , 305-314.		0
242	Bulk Properties of MOCVD-Deposited HfO[sub 2] Layers for High k Dielectric Applications. Journal of the Electrochemical Society, 2004, 151, F228.	2.9	16
243	Modification of Nanoporous Silica Structures by Fluorocarbon Plasma Treatment. Materials Research Society Symposia Proceedings, 2004, 812, F6.7.1.	0.1	3
244	Ellipsometric Porosimetry of Porous Low-k Films with Quazi-Closed Cavities. Materials Research Society Symposia Proceedings, 2004, 812, F5.4.1.	0.1	14
245	A Discussion of the Practical Importance of Positron Annihilation Lifetime Spectroscopy Percolation Threshold in Evaluation of Porous Low-KDielectrics. Japanese Journal of Applied Physics, 2004, 43, 247-248.	1.5	23
246	Superconductivity on the localization threshold and magnetic-field-tuned superconductor-insulator transition in TiN films. JETP Letters, 2004, 79, 337-341.	1.4	59
247	Morphological Control of Nanoporous Films by the Use of Functionalized Cyclodextrins as Porogens. Advanced Functional Materials, 2004, 14, 277-282.	14.9	36
248	Pore Structure of Modified Cyclic Silsesquioxane Thin Films Made Porous Using a Cyclodextrins-Based Porogen. Journal of Physical Chemistry B, 2004, 108, 8953-8959.	2.6	28
249	Internal matrix structure of low-Î¤ mesoporous silica and its relation to mechanical properties. Journal of Non-Crystalline Solids, 2004, 349, 189-199.	3.1	22
250	Porosity in plasma enhanced chemical vapor deposited SiCOH dielectrics: A comparative study. Journal of Applied Physics, 2003, 94, 3427-3435.	2.5	94
251	Low dielectric constant materials for microelectronics. Journal of Applied Physics, 2003, 93, 8793-8841.	2.5	1,494
252	Structural Characterization of Mesoporous Organosilica Films for Ultralow-kDielectrics. Journal of Physical Chemistry B, 2003, 107, 4280-4289.	2.6	107

#	Article	IF	Citations
253	The Removal of Copper Oxides by Ethyl Alcohol Monitored In Situ by Spectroscopic Ellipsometry. Journal of the Electrochemical Society, 2003, 150, G300.	2.9	57
254	Diffusion barrier integrity evaluation by ellipsometric porosimetry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 220.	1.6	42
255	Critical properties of nanoporous low dielectric constant films revealed by Brillouin light scattering and surface acoustic wave spectroscopy. Applied Physics Letters, 2002, 80, 4594-4596.	3.3	60
256	Comparative study of SiOCH low-k films with varied porosity interacting with etching and cleaning plasma. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1923.	1.6	141
257	Properties of porous HSQ-based films capped by plasma enhanced chemical vapor deposition dielectric layers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 109.	1.6	27
258	Characteristics of low-k and ultralow-k PECVD deposited SiCOH films.. Materials Research Society Symposia Proceedings, 2002, 716, 1231.	0.1	11
259	Determination of Youngâ€™s Modulus of Porous Low-k Films by Ellipsometric Porosimetry. Electrochemical and Solid-State Letters, 2002, 5, F29.	2.2	99
260	Strength-porosity relationship of nanoporous MSSQ films characterised by Brillouin Light Scattering and Surface Acoustic Wave Spectroscopy. Materials Research Society Symposia Proceedings, 2002, 716, 7171.	0.1	1
261	Ellipsometric study of the change in the porosity of silica xerogels after chemical modification of the surface with hexamethyldisilazane. Analytical and Bioanalytical Chemistry, 2002, 374, 654-657.	3.7	14
262	Comparison of techniques to characterise the density, porosity and elastic modulus of porous low-k SiO2 xerogel films. Microelectronic Engineering, 2002, 60, 133-141.	2.4	66
263	Comparative study of PECVD SiOCH low-k films obtained at different deposition conditions. Microelectronic Engineering, 2002, 64, 361-366.	2.4	23
264	Enhancement of ALCVDâ„¢ TiN growth on Siâ€“Oâ€“C and Î±-SiC:H films by O2-based plasma treatments. Microelectronic Engineering, 2002, 60, 59-69.	2.4	26
265	Non-destructive characterisation of porous low-k dielectric films. Microelectronic Engineering, 2002, 64, 335-349.	2.4	157
266	Comparative study of porous SOG films with different non-destructive instrumentation. , 2001, , .		1
267	Controllable Change of Porosity of 3-Methylsilane Low-k Dielectric Film. Electrochemical and Solid-State Letters, 2001, 4, F3.	2.2	35
268	Modification of Low-K SiCOH Film Porosity by a HF Solution. Solid State Phenomena, 2001, 76-77, 135-138.	0.3	2
269	Silicon Surface Cleaning after Spacer Dry Etching. Solid State Phenomena, 2001, 76-77, 303-306.	0.3	1
270	Characterization of Cu surface cleaning by hydrogen plasma. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1201.	1.6	89

#	Article	IF	Citations
271	Comparative Study of Pore Size of Low-Dielectric-Constant Porous Spin-on-Glass Films Using Different Methods of Nondestructive Instrumentation. Japanese Journal of Applied Physics, 2001, 40, L323-L326.	1.5	40
272	Characterisation of Low-K Dielectric Films by Ellipsometric Porosimetry. Materials Research Society Symposia Proceedings, 2000, 612, 421.	0.1	18
273	Mesoscopic SNS junctions on the basis of superconducting PtSi films. Physica B: Condensed Matter, 2000, 284-288, 1860-1861.	2.7	3
274	Low temperature oxidation and selective etching of chemical vapor deposition a-SiC:H films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1281.	1.6	26
275	Determination of pore size distribution in thin films by ellipsometric porosimetry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1385.	1.6	472
276	Proximity effects and Andreev reflection in a mesoscopic SNS junction with perfect NS interfaces. Physical Review B, 2000, 61, 11340-11343.	3.2	15
277	Characterization of HF Cleaning of Ion-Implanted Si Surfaces. Solid State Phenomena, 1999, 65-66, 271-274.	0.3	0
278	Post Dry-Etch Cleaning Issues of an Organic Low-K Dielectric. Solid State Phenomena, 1999, 65-66, 89-92.	0.3	3
279	The Optimization of the Cleaning to Remove Residual Bonds of Si-C and Si-F after Fluorocarbon Plasma Etch on the Silicon Surface. Solid State Phenomena, 1999, 65-66, 291-0.	0.3	1
280	Process integration induced thermodesorption from SiO[sub 2]/SiLK resin dielectric based interconnects. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2136.	1.6	7
281	Surface characterization of a low dielectric constant polymerâ€“SiLK[sup â^—] polymer, and investigation of its interface with Cu. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2336.	1.6	28
282	Analyses of Post Metal Etch Cleaning in Downstream â€‰Hâ€‰2â€‰Oâ€‰â€‰â€‰â€‰Based Plasma Followed by a Wet Chemistry. Journal of the Electrochemical Society, 1999, 146, 3843-3851.	2.9	8
283	Characterization of the Post Dryâ€Etch Cleaning of Silicon for Tiâ€Selfâ€Aligned Silicide Technology. Journal of the Electrochemical Society, 1999, 146, 1549-1556.	2.9	7
284	Effects of oxygen and fluorine on the dry etch characteristics of organic low-k dielectrics. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 372.	1.6	63
285	Applications of in-line oxygen monitoring to a rapid thermal processing tool: diagnosing gas flow dynamics and silicidation processes. Materials Science in Semiconductor Processing, 1999, 2, 341-348.	4.0	0
286	Nondestructive Determination of Pore Size Distribution in Thin Films Deposited on Solid Substrates. Electrochemical and Solid-State Letters, 1999, 2, 192.	2.2	61
287	Calculation of Pore Size Distribution in the Ellipsometric Porosimetry: Method and Reliability. Materials Research Society Symposia Proceedings, 1999, 565, 81.	0.1	5
288	Morphology of corrosion pits in aluminum thin film metallizations. Journal of Solid State Electrochemistry, 1998, 2, 150-155.	2.5	8

#	Article	IF	Citations
289	Characterisation of HF-last cleaning of ion-implanted Si surfaces. Materials Science in Semiconductor Processing, 1998, 1, 107-117.	4.0	10
290	Evaluation of Post Metal Etch Cleaning by Analyzing the Chemical Compositions and Distributions on the Etched Al Surface. Solid State Phenomena, 1998, 65-66, 177-180.	0.3	0
291	Limitation of HFâ€Based Chemistry for Deepâ€Submicron Contact Hole Cleaning on Silicides. Journal of the Electrochemical Society, 1998, 145, 3240-3246.	2.9	3
292	Surface processes occurring on TiSi[sub 2] and CoSi[sub 2] in fluorine-based plasmas: Afterglow of a NF[sub 3] plasma. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 164.	1.6	9
293	Oxidation and roughening of silicon during annealing in a rapid thermal processing chamber. Journal of Applied Physics, 1998, 83, 3614-3619.	2.5	13
294	XPS Study of the Cleaning Efficiency by Ozone Processes of the Protective Films Formed by Reactive Ion Etching of Co and Ti Silicide. Solid State Phenomena, 1998, 65-66, 139-142.	0.3	0
295	Plasma etching of organic low-dielectric-constant polymers: comparative analysis. Materials Research Society Symposia Proceedings, 1998, 511, 247.	0.1	7
296	Electric Field Direct Force in Electromigration Mechanism. Materials Research Society Symposia Proceedings, 1998, 516, 195.	0.1	0
297	Surface processes occurring on TiSi2 and CoSi2 in fluorine-based plasmas. Reactive ion etching in CF4/CHF3 plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 3005-3014.	2.1	6
298	Quantum transport in ultrathin CoSi2 polycrystalline films. Solid State Communications, 1997, 104, 147-150.	1.9	0
299	Adsorption of molecular fluorine on the Si(100) surface: an ellipsometric study. Surface Science, 1996, 347, 97-104.	1.9	4
300	The role of the negatively charged (Si3â^'Siâ^'F2)â^' complexes in interactions of fluorine with the (111) surface of silicon. Journal of Structural Chemistry, 1996, 37, 11-17.	1.0	1
301	Oscillation of the scattering time in a 2D electron system with oval antidots. Solid-State Electronics, 1996, 40, 441-446.	1.4	1
302	Highâ€rate deposition of aâ€Si:H films using a flow plasmaâ€“chemical method with electron beam activation. Journal of Applied Physics, 1996, 79, 7274-7277.	2.5	18
303	Kinetics and Mechanism of the Etching of CoSi2 in HFâ€based Solutions. Journal of the Electrochemical Society, 1996, 143, 3245-3251.	2.9	13
304	Silicon surface cleaning using XeF2 gas treatment. Applied Surface Science, 1995, 90, 191-194.	6.1	6
305	Charge capture in heterostructures with disordered antidot lattice. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 322-324.	3.5	0
306	Composition, Structure and Modification of Passivating Films on Semiconductors Deposited at Low Temperatures. Materials Science Forum, 1995, 185-188, 65-72.	0.3	1

#	Article	IF	Citations
307	The change of properties of the dehydroxylated SiO2 layer surface during gas adsorption in the temperature range 20â€“400Â°C. Materials Letters, 1991, 11, 119-123.	2.6	7
308	Adsorption and consumption of atomic fluorine on SiO2 surface. Reaction Kinetics and Catalysis Letters, 1989, 40, 247-251.	0.6	0
309	Universal conductance fluctuations of Î´-doped GaAs structures of small size. Solid State Communications, 1989, 70, 773-775.	1.9	1
310	Porous structure of SiO2 films synthesized at low temperature and pressure. Thin Solid Films, 1989, 171, 43-52.	1.8	36
311	Initial stages of the interaction of nitrous oxide and oxygen with the (100) silicon surface under low pressures. Reactivity of Solids, 1989, 7, 1-18.	0.3	16
312	Kinetics of Gas - Solid Interactions. Studies in Surface Science and Catalysis, 1982, 9, 265.	1.5	0
313	On the nature of the rate limiting step of the reaction of interaction of monocrystalline germanium with gaseous bromine. Surface Science, 1979, 88, 427-438.	1.9	7
314	Ellipsometric study of the interaction of a germanium monocrystal with bromine. Reaction Kinetics and Catalysis Letters, 1976, 4, 413-418.	0.6	1
315	Non-destructive characterisation of porosity and pore size distribution in porous low-k dielectric films. , 0, , .		0
316	Nanoporous polymer film properties from Brillouin light scattering and surface acoustic wave spectroscopy. , 0, , .		0
317	Nondestructive stiffness and density characterization of porous low-k films by surface acoustic wave spectroscopy. , 0, , .		0
318	Challenges of clean/strip processing for Cu/low-k technology. , 0, , .		6
319	Integration of Low-k Dielectric Films in Damascene Processes. , 0, , 199-250.		9
320	Spin-on Dielectric Materials. , 0, , 33-83.		12
321	Low and Ultralow Dielectric Constant Films Prepared by Plasma-enhanced Chemical Vapor Deposition. , 0, , 1-32.		15
322	Porosity of Low Dielectric Constant Materials. , 0, , 85-136.		7
323	Ultra-low-k material cryoetching plasma process for interconnects. SPIE Newsroom, 0, , .	0.1	1